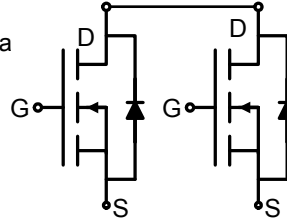


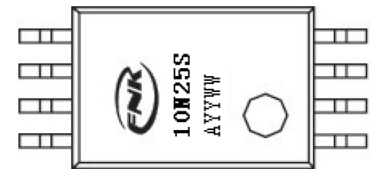
## FNK N-Channel Enhancement Mode Power MOSFET

### Description

The FNK10N25S uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



Schematic diagram



Marking and pin assignment

### General Features

- $V_{DS} = 20V, I_d = 8A$   
 $R_{DS(ON)} < 22m\Omega @ V_{GS}=2.5V$   
 $R_{DS(ON)} < 16m\Omega @ V_{GS}=4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

### Application

- Battery protection
- Load switch
- Power management



TSSOP-8 top view



### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
FNK10N25S	FNK10N25S	TSSOP-8L	Ø330mm	12 mm	3000 units

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous	$I_D$	8	A
Drain Current-Pulsed (Note 1)	$I_{DM}$	32	A
Maximum Power Dissipation	$P_D$	1.5	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	$^\circ C/W$
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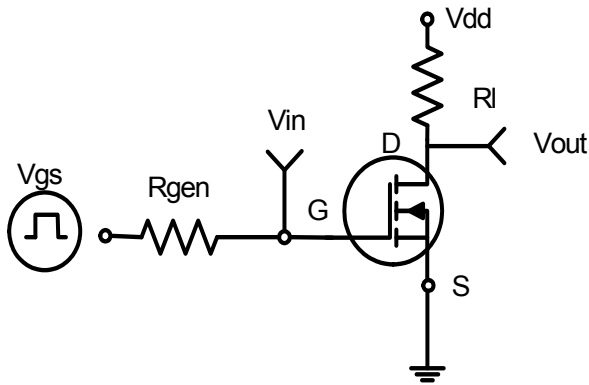
### Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

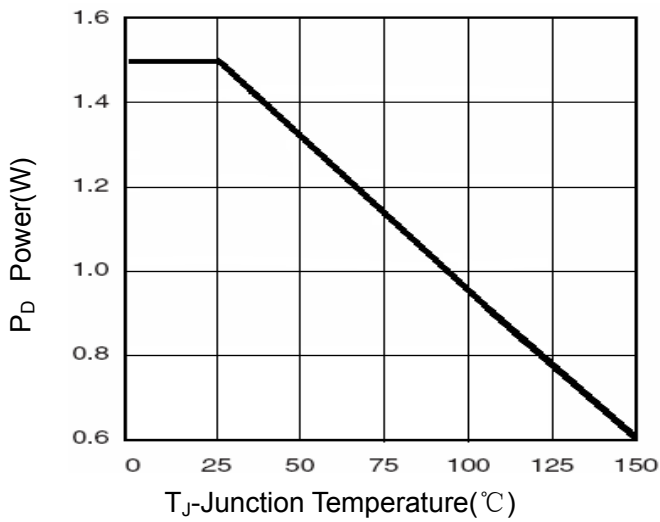
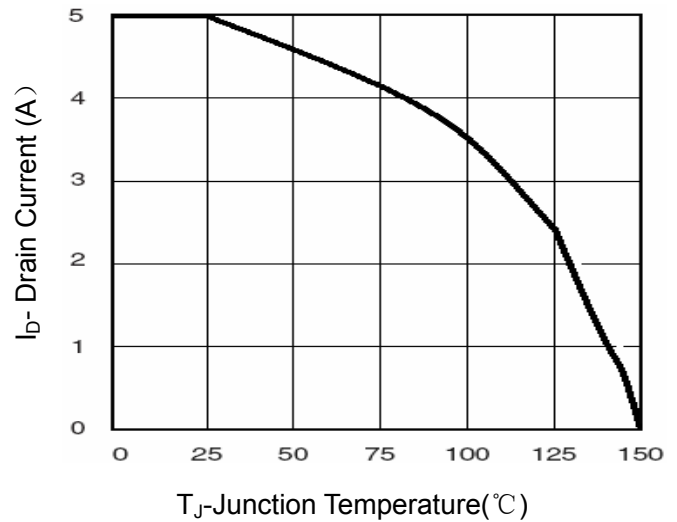
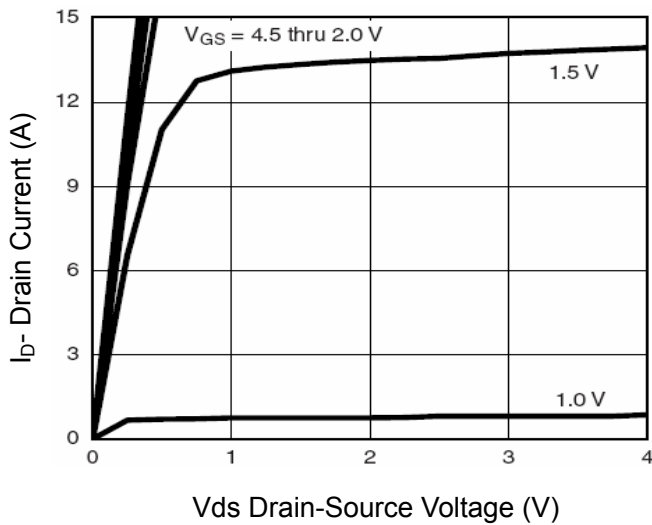
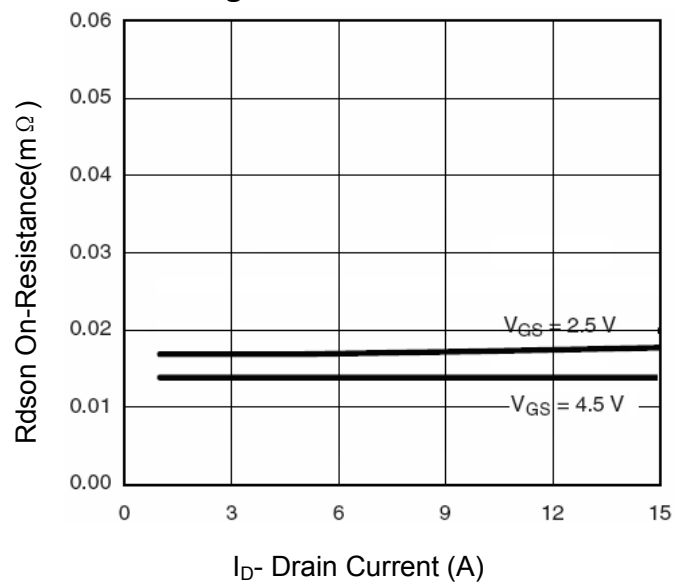
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	20	22	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$	-	-	1	$\mu A$

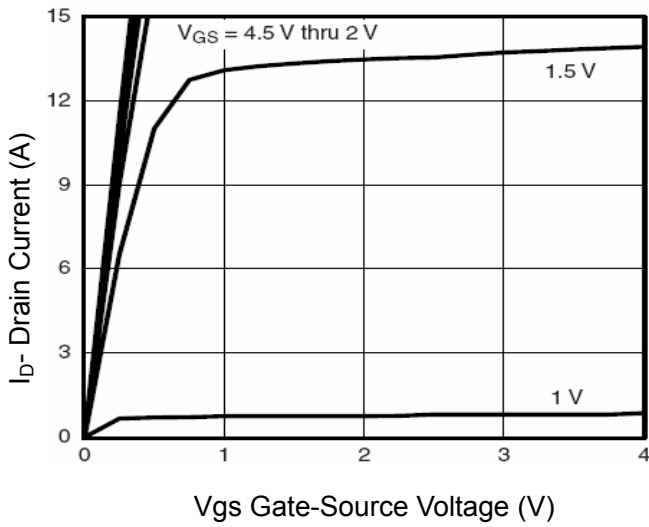
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.65	1.2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=2.5V, I_D=4.5 A$	-	16	22	m $\Omega$
		$V_{GS}=4.5V, I_D=5A$	-	13	16	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=15V, I_D=5A$	8	-	-	S
<b>Dynamic Characteristics (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0MHz$	-	780	-	PF
Output Capacitance	$C_{oss}$		-	140	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	80	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=1A$ $V_{GS}=4.5V, R_{GEN}=6\Omega$	-	9	-	nS
Turn-on Rise Time	$t_r$		-	30	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	35	-	nS
Turn-Off Fall Time	$t_f$		-	10	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=10V, I_D=5A, V_{GS}=4.5V$	-	11.4	-	nC
Gate-Source Charge	$Q_{gs}$		-	2.3	-	nC
Gate-Drain Charge	$Q_{gd}$		-	2.9	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=1A$	-	-	1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	5	A

### Notes:

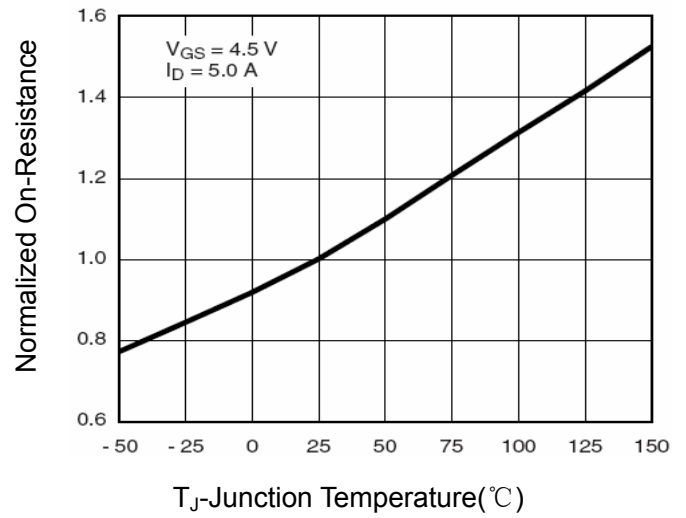
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

**Typical Electrical and Thermal Characteristics**

**Figure 1: Switching Test Circuit**

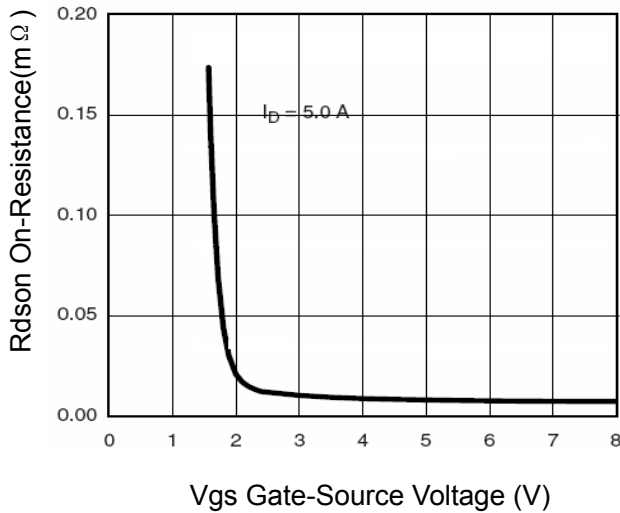
**Figure 2: Switching Waveforms**

**Figure 3 Power Dissipation**

**Figure 4 Drain Current**

**Figure 5 Output Characteristics**

**Figure 6 Drain-Source On-Resistance**



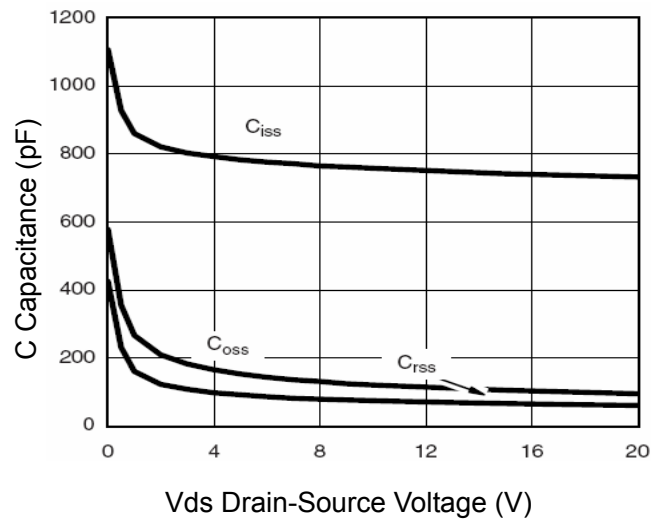
Vgs Gate-Source Voltage (V)  
**Figure 7 Transfer Characteristics**



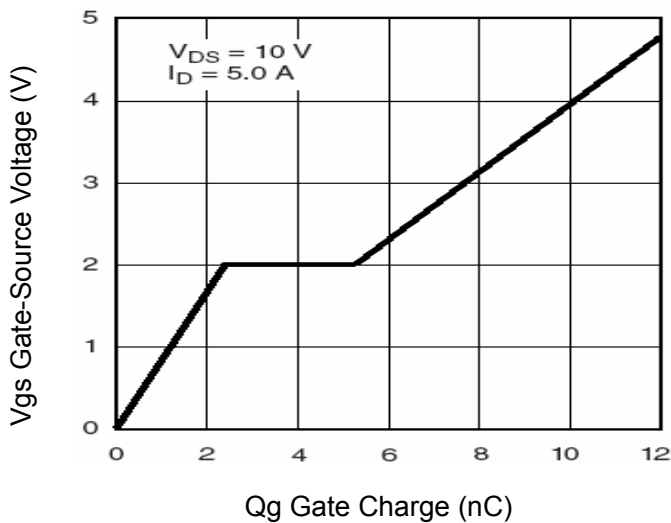
T<sub>J</sub>-Junction Temperature(°C)  
**Figure 8 Drain-Source On-Resistance**



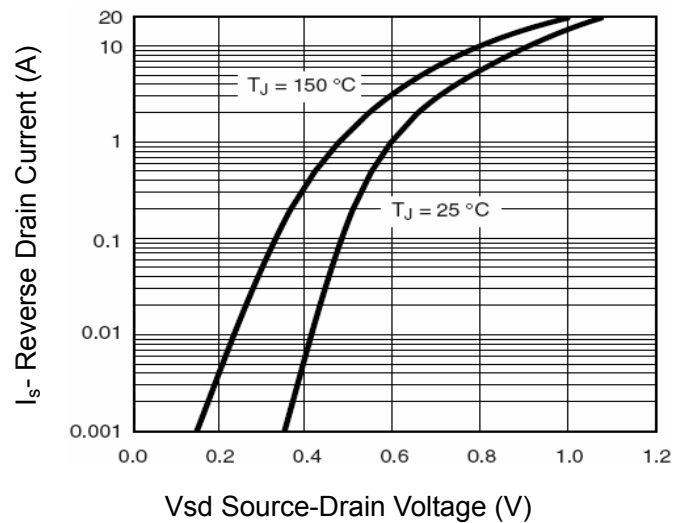
Vgs Gate-Source Voltage (V)  
**Figure 9 Rdson vs Vgs**



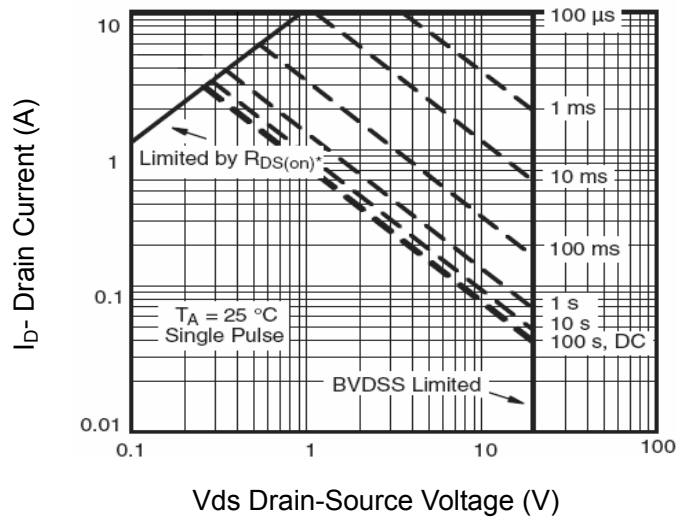
Vds Drain-Source Voltage (V)  
**Figure 10 Capacitance vs Vds**



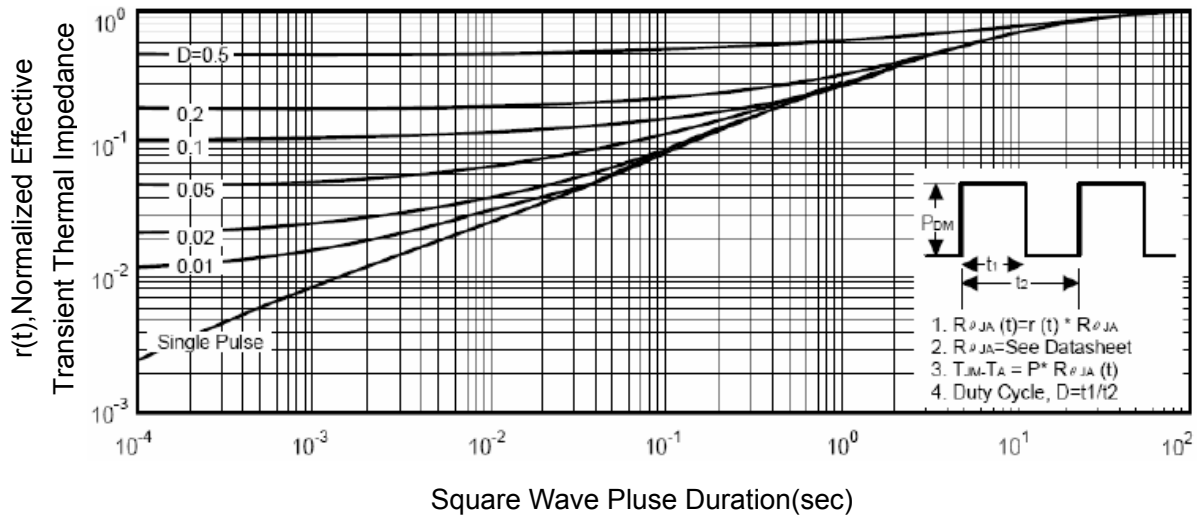
Qg Gate Charge (nC)  
**Figure 11 Gate Charge**



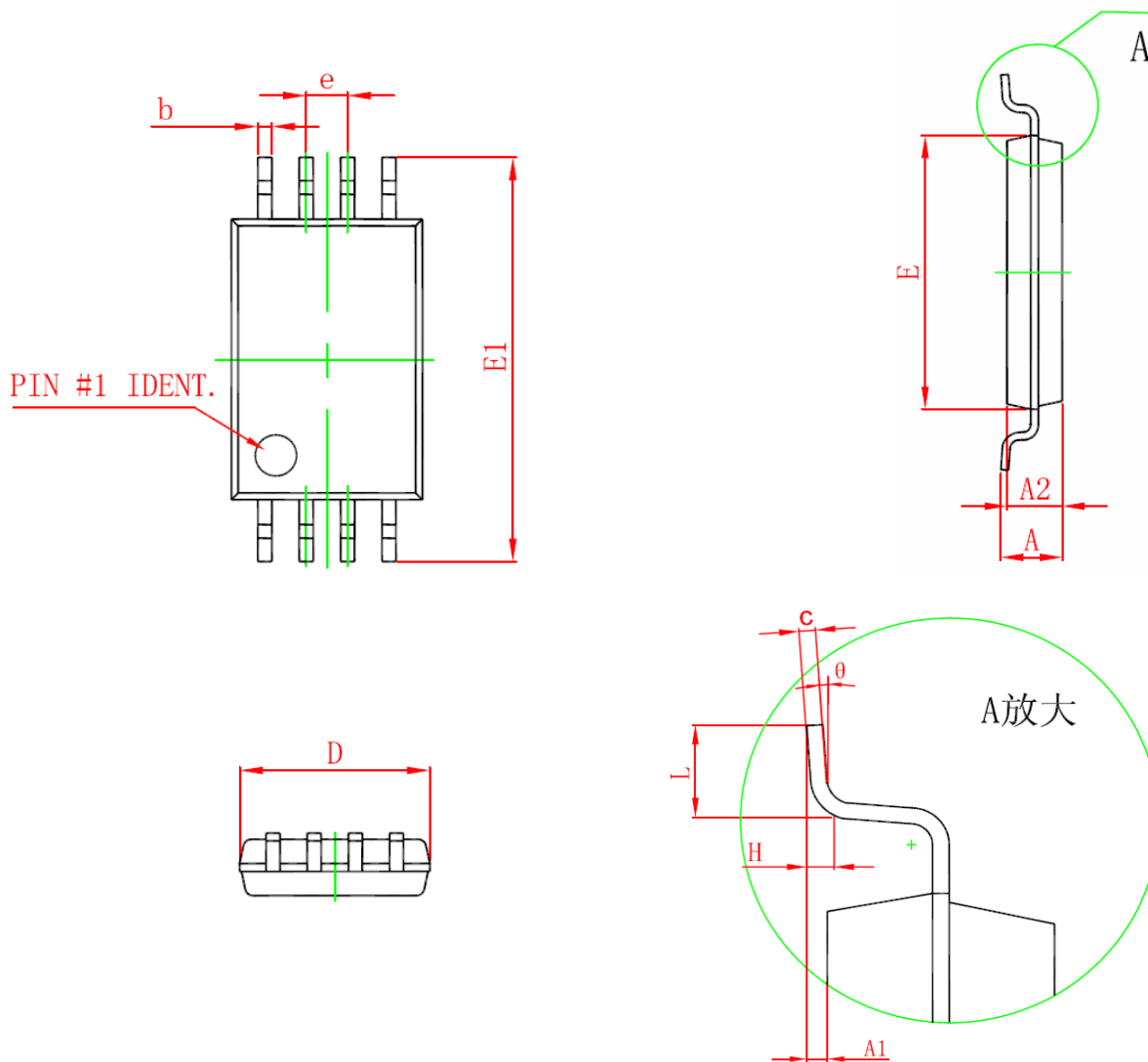
Vsd Source-Drain Voltage (V)  
**Figure 12 Source- Drain Diode Forward**



**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

**TSSOP-8 PACKAGE INFORMATION**


Symbol	Dimensions In Millimeters	
	Min	Max
D	2.900	3.100
E	4.300	4.500
b	0.190	0.300
c	0.090	0.200
E1	6.250	6.550
A		1.100
A2	0.800	1.000
A1	0.020	0.150
e	0.65(BSC)	
L	0.500	0.700
H	0.25(TYP)	
$\theta$	1°	7°

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- FNK will supply the best possible product for customers!